

Figure 1A
(PRIOR ART)

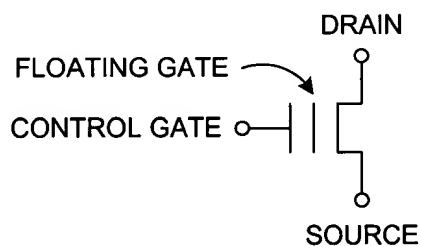


Figure 1B
(PRIOR ART)

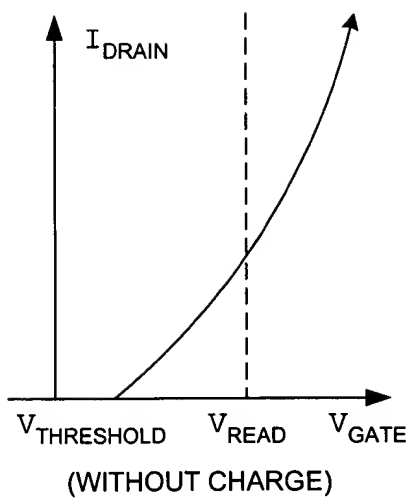


Figure 1C
(PRIOR ART)

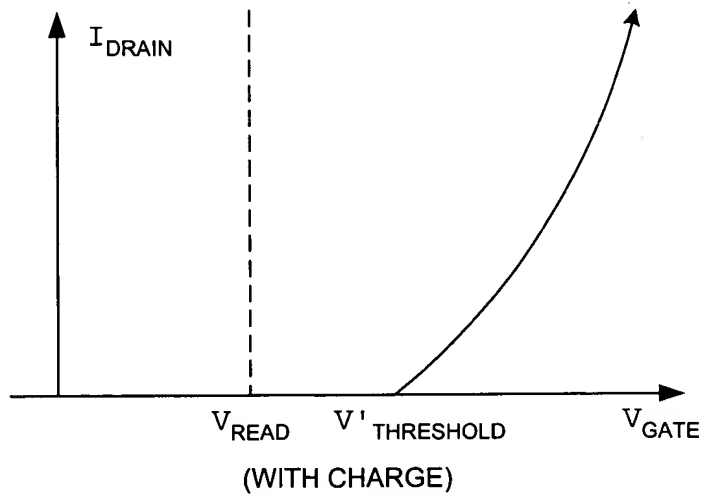


Figure 1D
(PRIOR ART)

**Batteryless, oscillatorless, binary time cell usable as an horological device
with associated programming methods and devices**

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CALCULATION OF NV MEMORY CELL RETENTION CHARACTERISTICS

					Seconds	Time Period
q0, C	m0, kg	kb, J/K	h, J-s	hb, J-s	31536000	1 year
1.6022E-019	9.1095E-031	1.38062E-023	6.62617E-034	1.05459E-034	94608000	3 years
					1.9E+008	6 years
b0, eV (barrier)	ϵ_l	mr, effective mass ratio	T, K degree		2.8E+017	9 years
	2.9	3.9	0.5	300	3.8E+008	12 years
					4.7E+008	15 years
C	b				9.1E+009	18 years
1.0630E-006	2.3854E+008				6.6E+008	21 years
					7.6E+008	24 years
					8.5E+008	27 years
					9.5E+008	30 years
Lfg um	0.6000	Channel length of floating gate device				
Wfg um	1000.0000	Channel width of floating gate device.				
Hfg um	0.0900	Thickness of floating gate polysilicon conductor				
Wrx um	0.5000	Width of floating gate overlapping shallow trench isolation				
Ttunox A	80	Tunnel oxide thickness				
Tono A	190	Thickness of Oxide-Nitride-Oxide dielectric between floating gate and control gate for capacitive coupling				
Tswox A	300	Thickness of sidewall oxide between floating gate and control gate for sidewall coupling				
Xfd um	0.0500	Length of floating gate overlapping drain region of the floating gate MOSFET				
Xfs um	0.3500	Length of floating gate overlapping source region of the floating gate MOSFET				
Ainj um ²	0.0438	Area of the electron tunneling region between the floating gate and the source for resetting the floating gate charge				
Cfc fF	1089.5358	Capacitance between the floating gate and the control gate				
Cfsx fF	0.4313	Capacitance between the floating gate and the silicon substrate				
Cfd fF	0.1078	Capacitance between the floating gate and the drain				
Cfs fF	0.7547	Capacitance between the floating gate and the source				
Cfg fF	1090.8295	Total floating gate capacitance				
Cr,wl	0.9988	Control gate to floating gate coupling ratio				
Cr,src	0.0007	Source junction to floating gate coupling ratio				
Vt,fg V	0.90	Threshold voltage of floating gate MOSFET				
Verase	0.00	Erase voltage applied to the source(not used here, set to zero)				
Vfg,ini	-5.00	Initial floating charged voltage				
Va	0.00	Actual erase voltage (equal to applied + charge stored on the floating)				
S	3.76E+016	Derived parameter in the floating gate "erase" equation				
X	1.27E+011	Derived parameter in the floating gate "erase" equation				

Figure 1E
(PRIOR ART)

t, sec.	Vt,fg
0.00001	5.907
31536000	5.894
63072000	5.882
94608000	5.871
1.3E+008	5.861
1.6E+008	5.852
1.9E+008	5.843
2.2E+008	5.835
2.5E+008	5.827
2.8E+008	5.820
3.2E+008	5.814
3.5E+008	5.807
3.8E+008	5.801
4.1E+008	5.795
4.4E+008	5.790
4.7E+008	5.785
5E+008	5.780
5.4E+008	5.775
5.7E+008	5.770
6E+008	5.766
6.3E+008	5.762
6.6E+008	5.757
6.9E+008	5.753
7.3E+008	5.750
7.6E+008	5.746
7.9E+008	5.742
8.2E+008	5.739
8.5E+008	5.735
8.8E+008	5.732
9.1E+008	5.729
9.5E+008	5.726

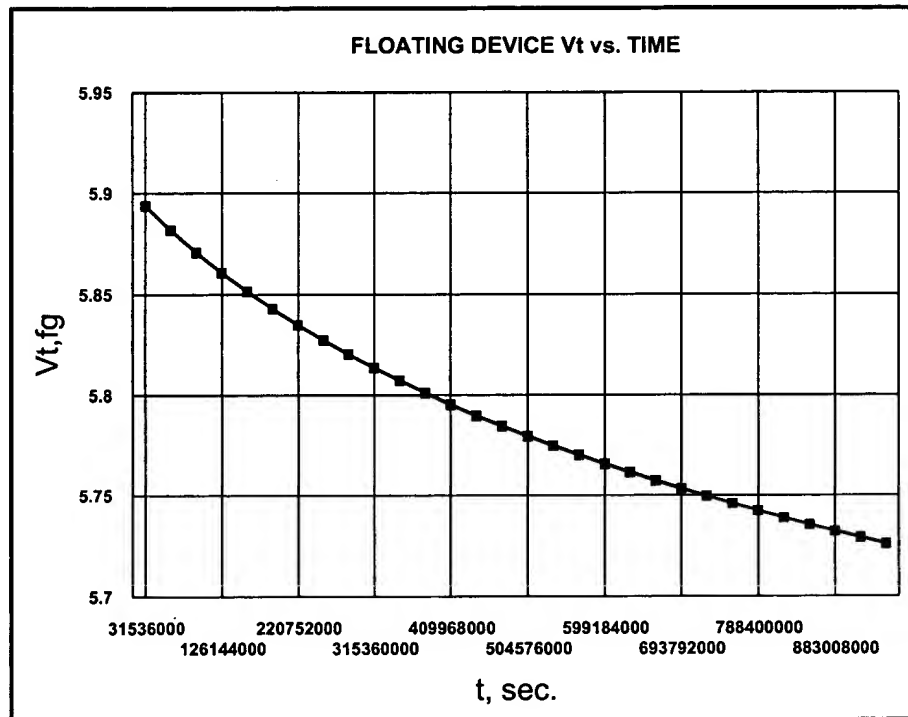


Figure 1F
 (PRIOR ART)

Batteryless, oscillatorless, binary time cell usable as an horological device
with associated programming methods and devices

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CALCULATION OF NV MEMORY CELL RETENTION CHARACTERISTICS

					Seconds	Time Period
q0, C	m0, kg	kb, J/K	h, J-s	hb, J-s	60	1 minute
1.6022E-019	9.1095E-031	1.38062E-023	6.62617E-034	1.05459E-034	3600	1 hour
					86400	1 day
b0, eV (barrier)	ϵ_1	mr, effective mass ratio	T, K degree		604800	1 week
2.9	3.9	0.5	300		2592000	1 month
					31536000	1 year
C	b				1.3E+008	4 years
1.0630E-006	2.3854E+008				5E+008	16 years
					1E+009	32 years
Lfg um	0.6000	Channel length of floating gate device				
Wfg um	1000.0000	Channel width of floating gate device.				
Hfg um	0.0900	Thickness of floating gate polysilicon conductor				
Wrx um	0.5000	Width of floating gate overlapping shallow trench isolation				
Ttunox A	80	Tunnel oxide thickness				
Tono A	190	Thickness of Oxide-Nitride-Oxide dielectric between floating gate and control gate for capacitive coupling				
Tswox A	300	Thickness of sidewall oxide between floating gate and control gate for sidewall coupling				
Xfd um	0.0500	Length of floating gate overlapping drain region of the floating gate MOSFET				
Xfs um	0.3500	Length of floating gate overlapping source region of the floating gate MOSFET				
Ainj um ²	0.0438	Area of the electron tunneling region between the floating gate and the source for resetting the floating gate charge				
Cfc fF	1089.5358	Capacitance between the floating gate and the control gate				
Cfsx fF	0.4313	Capacitance between the floating gate and the silicon substrate				
Cfd fF	0.1078	Capacitance between the floating gate and the drain				
Cfs fF	0.7547	Capacitance between the floating gate and the source				
Cfg fF	1090.8295	Total floating gate capacitance				
Cr,wl	0.9988	Control gate to floating gate coupling ratio				
Cr,src	0.0007	Source junction to floating gate coupling ratio				
Vt,fg V	0.90	Threshold voltage of floating gate MOSFET				
Verase	0.00	Erase voltage applied to the source(not used here, set to zero)				
Vfg,ini	-5.00	Initial floating charged voltage				
Va	0.00	Actual erase voltage (equal to applied + charge stored on the floating)				
S	3.76E+016	Derived parameter in the floating gate "erase" equation				
X	1.27E+011	Derived parameter in the floating gate "erase" equation				

Figure 1G
(PRIOR ART)

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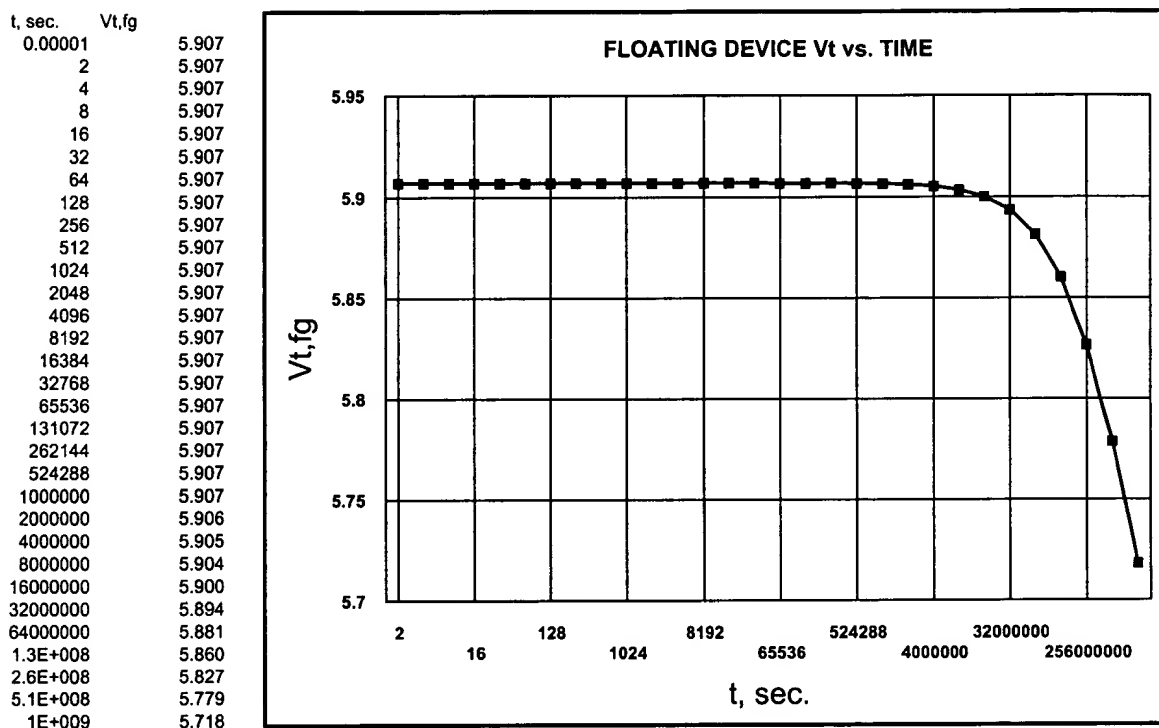


Figure 1H
 (PRIOR ART)

**Batteryless, oscillatorless, binary time cell usable as an horological device
with associated programming methods and devices**

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CALCULATION OF NV MEMORY CELL RETENTION CHARACTERISTICS

						Seconds	Time Period
q0, C	m0, kg	kb, J/K	h, J-s	hb, J-s		60	1 minute
1.6022E-019	9.1095E-031	1.38062E-023	6.62617E-034	1.05459E-034		3600	1 hour
						86400	1 day
b0, eV (barrier)	ϵ_l	mr, effective mass ratio	T, K degree			604800	1 week
2.9	3.9	0.5	300			2592000	1 month
						31536000	1 year
C	b					1.3E+008	4 years
1.0630E-006	2.3854E+008					5E+008	16 years
						1E+009	32 years
Lfg um	0.6000	Channel length of floating gate device					
Wfg um	1000.0000	Channel width of floating gate device.					
Hfg um	0.0900	Thickness of floating gate polysilicon conductor					
Wrx um	0.5000	Width of floating gate overlapping shallow trench isolation					
Ttunox A	85	Tunnel oxide thickness					
Tono A	190	Thickness of Oxide-Nitride-Oxide dielectric between floating gate and control gate for capacitive coupling					
Tswox A	300	Thickness of sidewall oxide between floating gate and control gate for sidewall coupling					
Xfd um	0.0500	Length of floating gate overlapping drain region of the floating gate MOSFET					
Xfs um	0.3500	Length of floating gate overlapping source region of the floating gate MOSFET					
Ainj um ²	0.0438	Area of the electron tunneling region between the floating gate and the source for resetting the floating gate charge					
Cfc fF	1089.5358	Capacitance between the floating gate and the control gate					
Cfsx fF	0.4059	Capacitance between the floating gate and the silicon substrate					
Cfd fF	0.1015	Capacitance between the floating gate and the drain					
Cfs fF	0.7103	Capacitance between the floating gate and the source					
Cfg fF	1090.7534	Total floating gate capacitance					
Cr,wl	0.9989	Control gate to floating gate coupling ratio					
Cr,src	0.0007	Source junction to floating gate coupling ratio					
Vt,fg V	0.90	Threshold voltage of floating gate MOSFET					
Verase	0.00	Erase voltage applied to the source(not used here, set to zero)					
Vfg,ini	-5.00	Initial floating charged voltage					
Va	0.00	Actual erase volatge (equal to applied + charge stored on the floating)					
S	4.09E+017	Derived parameter in the floating gate "erase" equation					
X	1.20E+011	Derived parameter in the floating gate "erase" equation					

Figure 11
(PRIOR ART)

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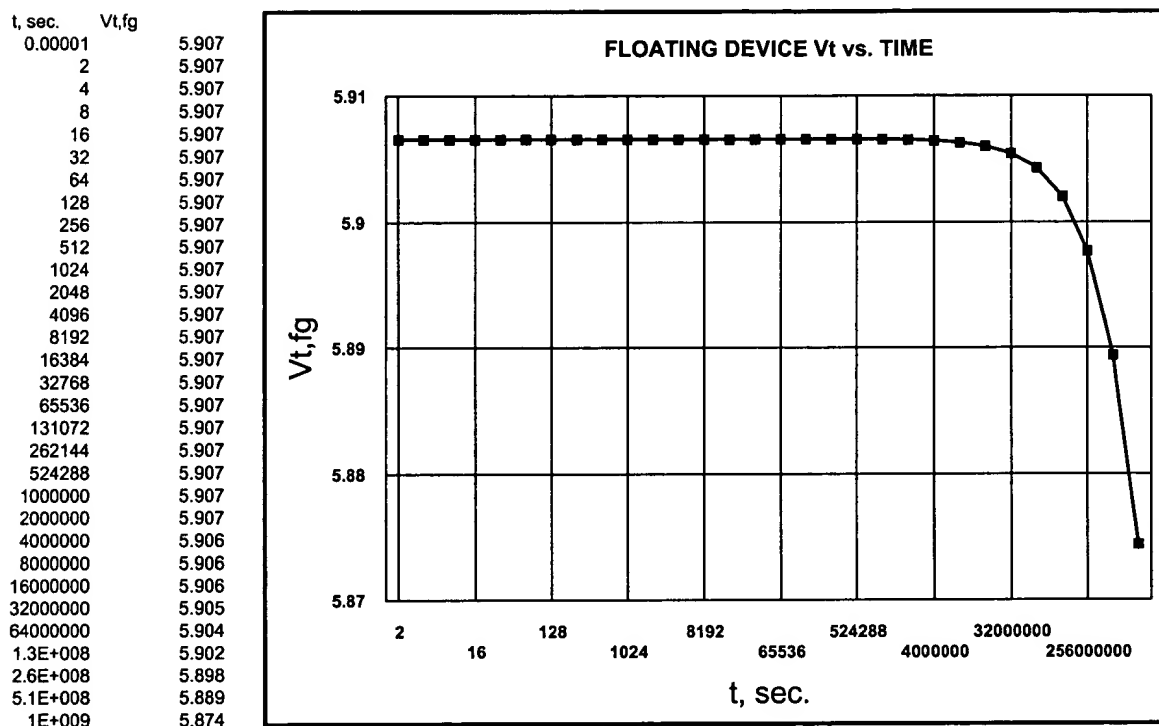


Figure 1J
 (PRIOR ART)

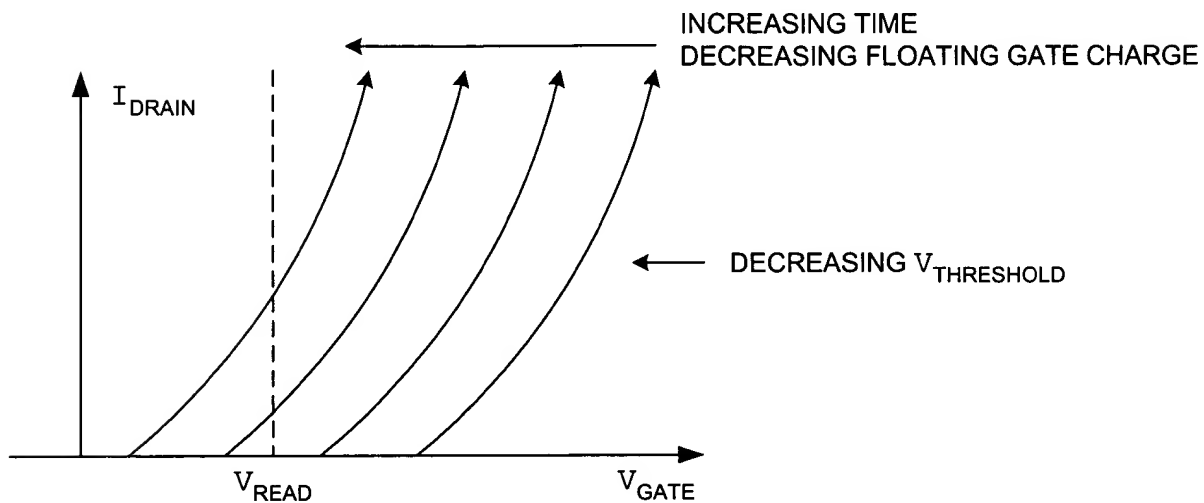


Figure 1K

**Batteryless, oscillatorless, binary time cell usable as an horological device
with associated programming methods and devices**

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CALCULATION OF NV MEMORY CELL RETENTION CHARACTERISTICS

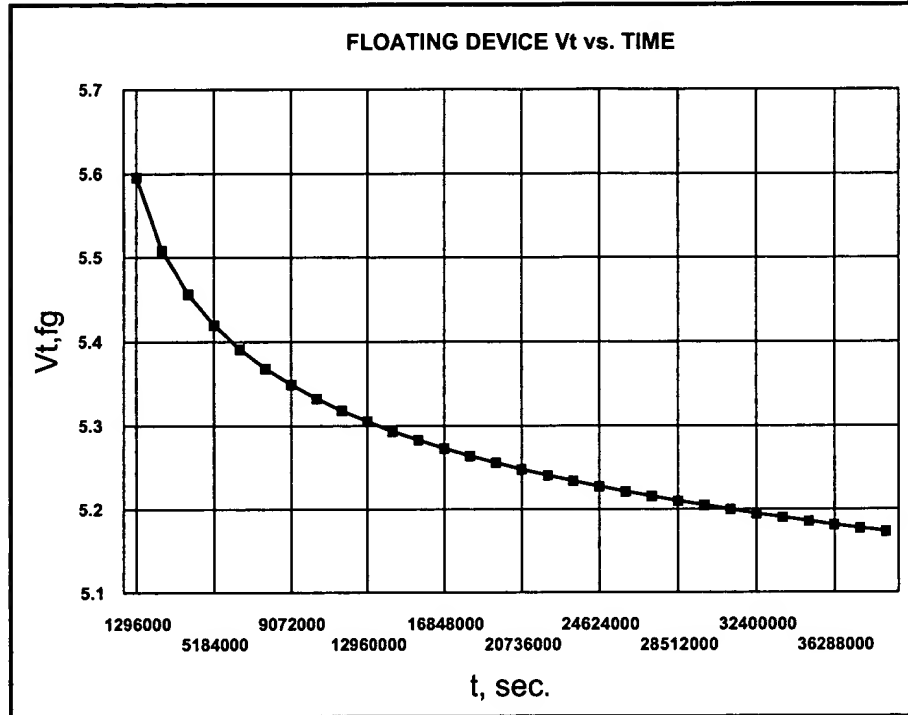
					Seconds	Time Period
q0, C	m0, kg	kb, J/K	h, J-s	hb, J-s	2592000	1 month
1.6022E-019	9.1095E-031	1.38062E-023	6.62617E-034	1.05459E-034	5184000	2 months
					7776000	3 months
b0, eV (barrier)	ϵ_1	mr, effective mass ratio	T, K degree		10368000	4 months
	2.9	3.9	0.5	300	12960000	5 months
					15552000	6 months
C	b				18144000	7 months
1.0630E-006	2.3854E+008				20736000	8 months
					23328000	9 months
					25920000	10 months
					28512000	11 months
					31104000	12 months
Lfg um	0.6000	Channel length of floating gate device			33696000	13 months
Wfg um	1000.0000	Channel width of floating gate device.			36288000	14 months
Hfg um	0.0900	Thickness of floating gate polysilicon conductor			38880000	15 months
Wrx um	0.5000	Width of floating gate overlapping shallow trench isolation			41472000	16 months
Ttunox A	65	Tunnel oxide thickness				
Tono A	190	Thickness of Oxide-Nitride-Oxide dielectric between floating gate and control gate for capacitive coupling				
Tswox A	300	Thickness of sidewall oxide between floating gate and control gate for sidewall coupling				
Xfd um	0.0500	Length of floating gate overlapping drain region of the floating gate MOSFET				
Xfs um	0.3500	Length of floating gate overlapping source region of the floating gate MOSFET				
Ainj um ²	0.0438	Area of the electron tunneling region between the floating gate and the source for resetting the floating gate charge				
Cfc fF	1089.5358	Capacitance between the floating gate and the control gate				
Cfsx fF	0.5308	Capacitance between the floating gate and the silicon substrate				
Cfd fF	0.1327	Capacitance between the floating gate and the drain				
Cfs fF	0.9288	Capacitance between the floating gate and the source				
Cfg fF	1091.1281	Total floating gate capacitance				
Cr,wl	0.9985	Control gate to floating gate coupling ratio				
Cr,src	0.0009	Source junction to floating gate coupling ratio				
Vt,fg V	0.90	Threshold voltage of floating gate MOSFET				
Verase	0.00	Erase voltage applied to the source(not used here, set to zero)				
Vfg,ini	-5.00	Initial floating charged voltage				
Va	0.00	Actual erase voltage (equal to applied + charge stored on the floating)				
S	2.93E+013	Derived parameter in the floating gate "erase" equation				
X	1.56E+011	Derived parameter in the floating gate "erase" equation				

Figure 1L

**Batteryless, oscillatorless, binary time cell usable as an horological device
with associated programming methods and devices**

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t, sec.	Vt,fg
0.00001	5.909
1296000	5.596
2592000	5.508
3888000	5.456
5184000	5.420
6480000	5.392
7776000	5.369
9072000	5.349
10368000	5.333
11664000	5.318
12960000	5.305
14256000	5.293
15552000	5.283
16848000	5.273
18144000	5.264
19440000	5.256
20736000	5.248
22032000	5.240
23328000	5.234
24624000	5.227
25920000	5.221
27216000	5.215
28512000	5.210
29808000	5.204
31104000	5.199
32400000	5.195
33696000	5.190
34992000	5.185
36288000	5.181
37584000	5.177
38880000	5.173

*Figure 1M*

**Batteryless, oscillatorless, binary time cell usable as an horological device
with associated programming methods and devices**

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CALCULATION OF NV MEMORY CELL RETENTION CHARACTERISTICS

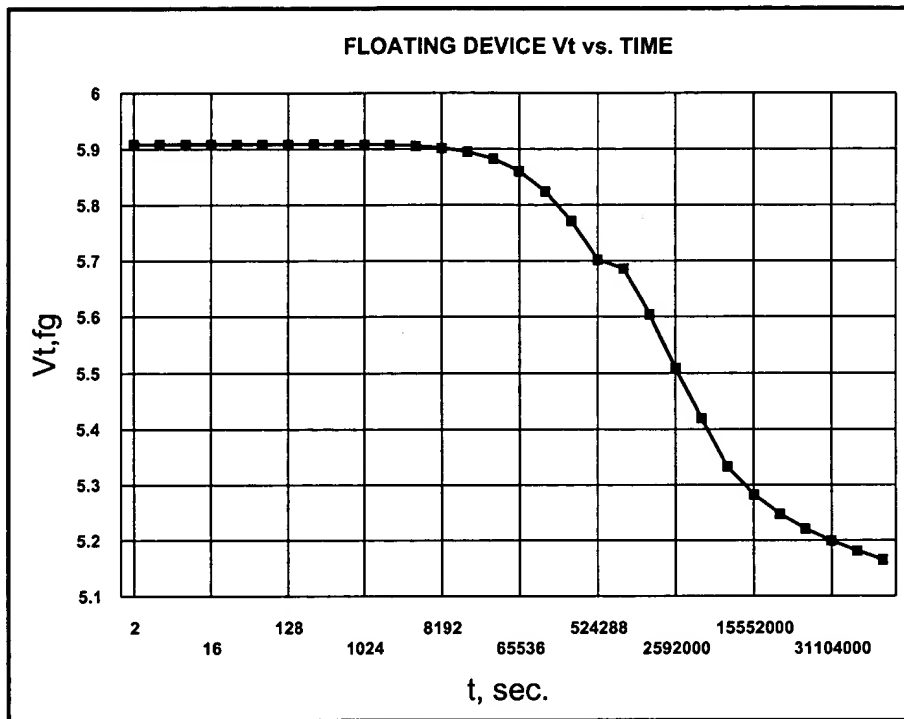
					Seconds	Time Period
q0, C	m0, kg	kb, J/K	h, J-s	hb, J-s	60	1 minute
1.6022E-019	9.1095E-031	1.38062E-023	6.62617E-034	1.05459E-034	3600	1 hour
					86400	1 day
b0, eV (barrier)	ϵ_l	mr, effective mass ratio	T, K degree		604800	1 week
2.9	3.9	0.5	300		1209600	2 weeks
					2592000	1 month
					5184000	2 months
C	b				10368000	4 months
1.0630E-006	2.3854E+008				15552000	6 months
					20736000	8 months
					25920000	10 months
					31104000	12 months
					36288000	14 months
					41472000	16 months
Lfg um	0.6000	Channel length of floating gate device				
Wfg um	1000.0000	Channel width of floating gate device.				
Hfg um	0.0900	Thickness of floating gate polysilicon conductor				
Wrx um	0.5000	Width of floating gate overlapping shallow trench isolation				
Ttunox A	65	Tunnel oxide thickness				
Tono A	190	Thickness of Oxide-Nitride-Oxide dielectric between floating gate and control gate for capacitive coupling				
Tswox A	300	Thickness of sidewall oxide between floating gate and control gate for sidewall coupling				
Xfd um	0.0500	Length of floating gate overlapping drain region of the floating gate MOSFET				
Xfs um	0.3500	Length of floating gate overlapping source region of the floating gate MOSFET				
Ainj um ²	0.0438	Area of the electron tunneling region between the floating gate and the source for resetting the floating gate charge				
Cfc fF	1089.5358	Capacitance between the floating gate and the control gate				
Cfsx fF	0.5308	Capacitance between the floating gate and the silicon substrate				
Cfd fF	0.1327	Capacitance between the floating gate and the drain				
Cfs fF	0.9288	Capacitance between the floating gate and the source				
Cfg fF	1091.1281	Total floating gate capacitance				
Cr,wl	0.9985	Control gate to floating gate coupling ratio				
Cr,src	0.0009	Source junction to floating gate coupling ratio				
Vt,fg V	0.90	Threshold voltage of floating gate MOSFET				
Verase	0.00	Erase voltage applied to the source(not used here, set to zero)				
Vfg,ini	-5.00	Initial floating charged voltage				
Va	0.00	Actual erase voltage (equal to applied + charge stored on the floating)				
S	2.93E+013	Derived parameter in the floating gate "erase" equation				
X	1.56E+011	Derived parameter in the floating gate "erase" equation				

Figure 1N

**Batteryless, oscillatorless, binary time cell usable as an horological device
with associated programming methods and devices**

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t, sec.	Vt, fg
0.00001	5.909
2	5.909
4	5.909
8	5.909
16	5.909
32	5.909
64	5.909
128	5.909
256	5.908
512	5.908
1024	5.908
2048	5.907
4096	5.905
8192	5.902
16384	5.895
32768	5.883
65536	5.861
131072	5.824
262144	5.771
524288	5.702
1048576	5.686
2097152	5.604
4194304	5.508
8388608	5.420
16777216	5.333
33554432	5.283
67108864	5.248
134217728	5.221
268435456	5.199
536870912	5.181
1073741824	5.166

*Figure 10*

**Batteryless, oscillatorless, binary time cell usable as an horological device
with associated programming methods and devices**

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CALCULATION OF NV MEMORY CELL RETENTION CHARACTERISTICS

					Seconds	Time Period
q0, C	m0, kg	kb, J/K	h, J-s	hb, J-s	60	1 minute
1.6022E-019	9.1095E-031	1.38062E-023	6.62617E-034	1.05459E-034	3600	1 hour
					86400	1 day
b0, eV (barrier)	ϵ_l	mr, effective mass ratio	T, K degree		604800	1 week
2.9		3.9	0.5	300	1209600	2 weeks
					2592000	1 month
C	b				5184000	2 months
1.0630E-006	2.3854E+008				10368000	4 months
					15552000	6 months
					20736000	8 months
					25920000	10 months
					31104000	12 months
					36288000	14 months
					41472000	16 months
Lfg um	0.6000	Channel length of floating gate device				
Wfg um	1000.0000	Channel width of floating gate device.				
Hfg um	0.0900	Thickness of floating gate polysilicon conductor				
Wrx um	0.5000	Width of floating gate overlapping shallow trench isolation				
Ttunox A	60	Tunnel oxide thickness				
Tono A	190	Thickness of Oxide-Nitride-Oxide dielectric between floating gate and control gate for capacitive coupling				
Tswox A	300	Thickness of sidewall oxide between floating gate and control gate for sidewall coupling				
Xfd um	0.0500	Length of floating gate overlapping drain region of the floating gate MOSFET				
Xfs um	0.3500	Length of floating gate overlapping source region of the floating gate MOSFET				
Ainj um ²	0.0438	Area of the electron tunneling region between the floating gate and the source for resetting the floating gate charge				
Cfc fF	1089.5358	Capacitance between the floating gate and the control gate				
Cfsx fF	0.5750	Capacitance between the floating gate and the silicon substrate				
Cfd fF	0.1438	Capacitance between the floating gate and the drain				
Cfs fF	1.0063	Capacitance between the floating gate and the source				
Cfg fF	1091.2608	Total floating gate capacitance				
Cr,wl	0.9984	Control gate to floating gate coupling ratio				
Cr,src	0.0009	Source junction to floating gate coupling ratio				
Vt,fg V	0.90	Threshold voltage of floating gate MOSFET				
Verase	0.00	Erase voltage applied to the source(not used here, set to zero)				
Vfg,ini	-5.00	Initial floating charged voltage				
Va	0.00	Actual erase voltage (equal to applied + charge stored on the floating)				
S	2.70E+012	Derived parameter in the floating gate "erase" equation				
X	1.69E+011	Derived parameter in the floating gate "erase" equation				

Figure 1P

t, sec.	Vt,fg
0.00001	5.909
2	5.909
4	5.909
8	5.909
16	5.909
32	5.909
64	5.909
128	5.908
256	5.907
512	5.904
1024	5.898
2048	5.888
4096	5.870
8192	5.838
16384	5.789
32768	5.721
65536	5.639
131072	5.549
262144	5.455
524288	5.360
1048576	5.341
2097152	5.250
4194304	5.152
8388608	5.067
16777216	4.985
33554432	4.938
67108864	4.906
134217728	4.881
268435456	4.861
536870912	4.844
1073741824	4.830

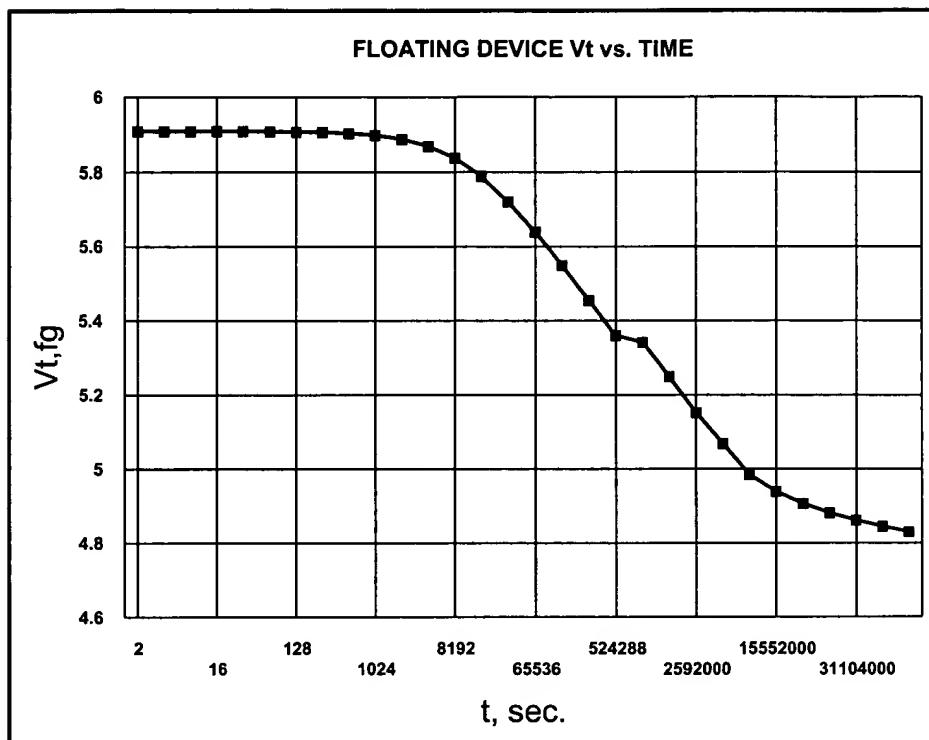


Figure 1Q

Batteryless, oscillatorless, binary time cell usable as an horological device
with associated programming methods and devices

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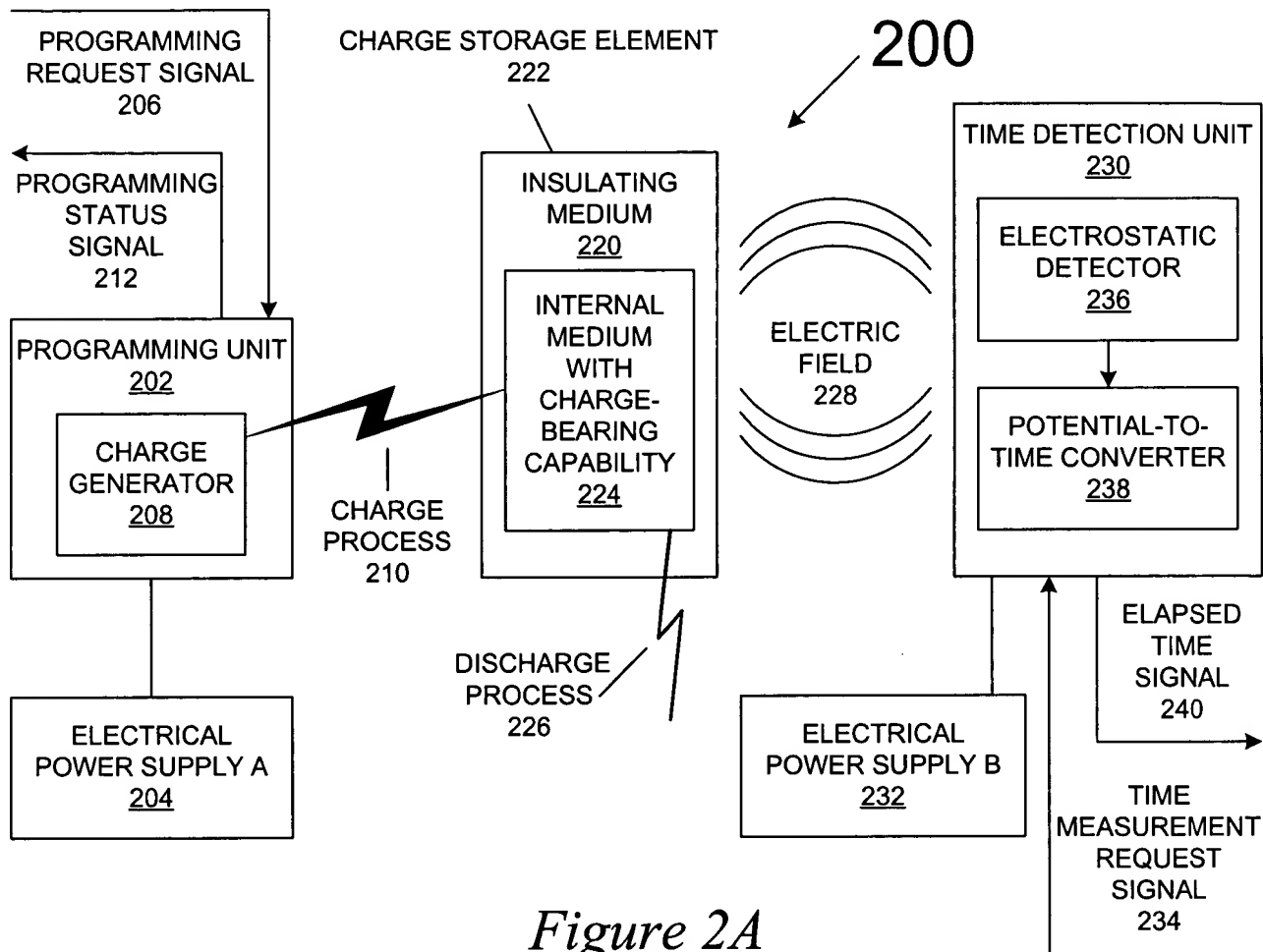


Figure 2A

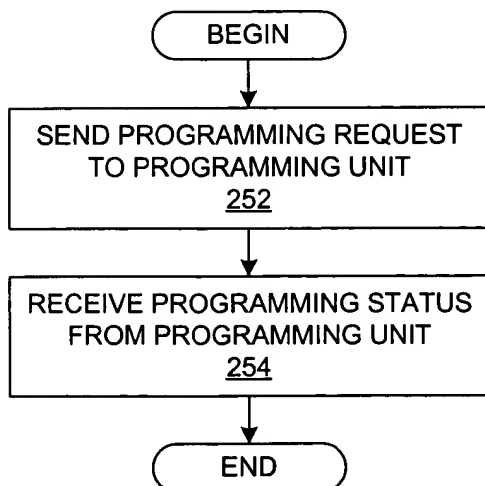


Figure 2B

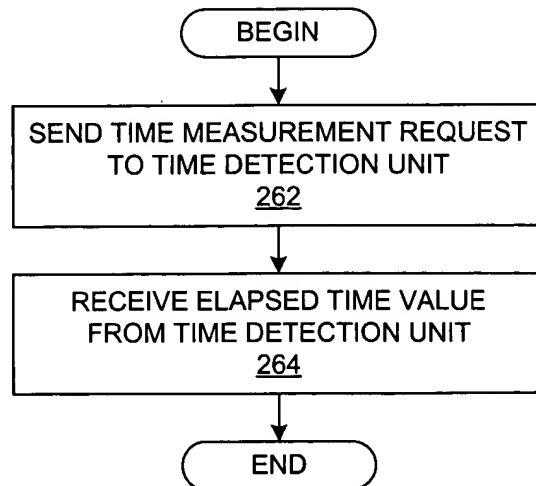


Figure 2C

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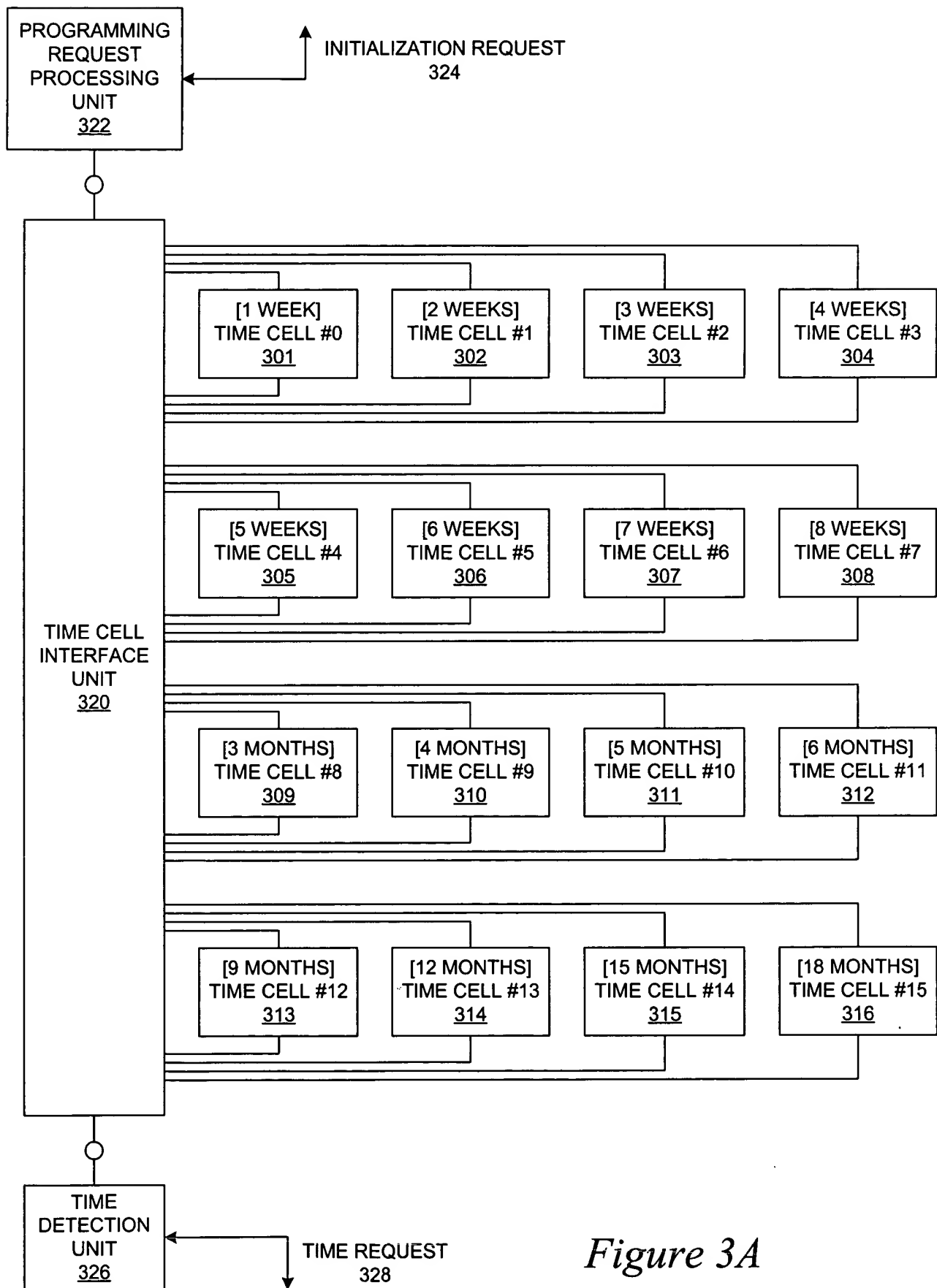


Figure 3A

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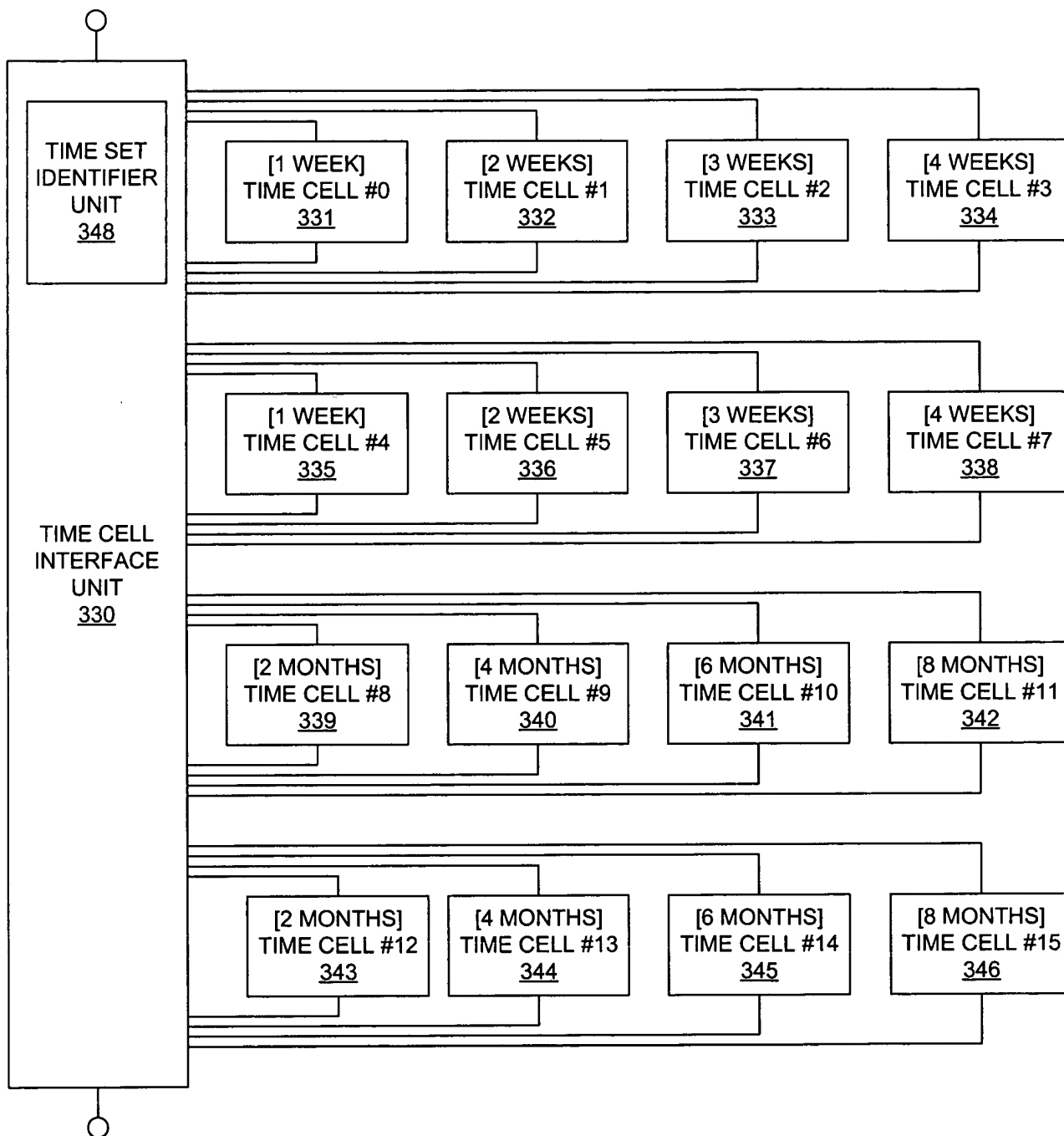


Figure 3B

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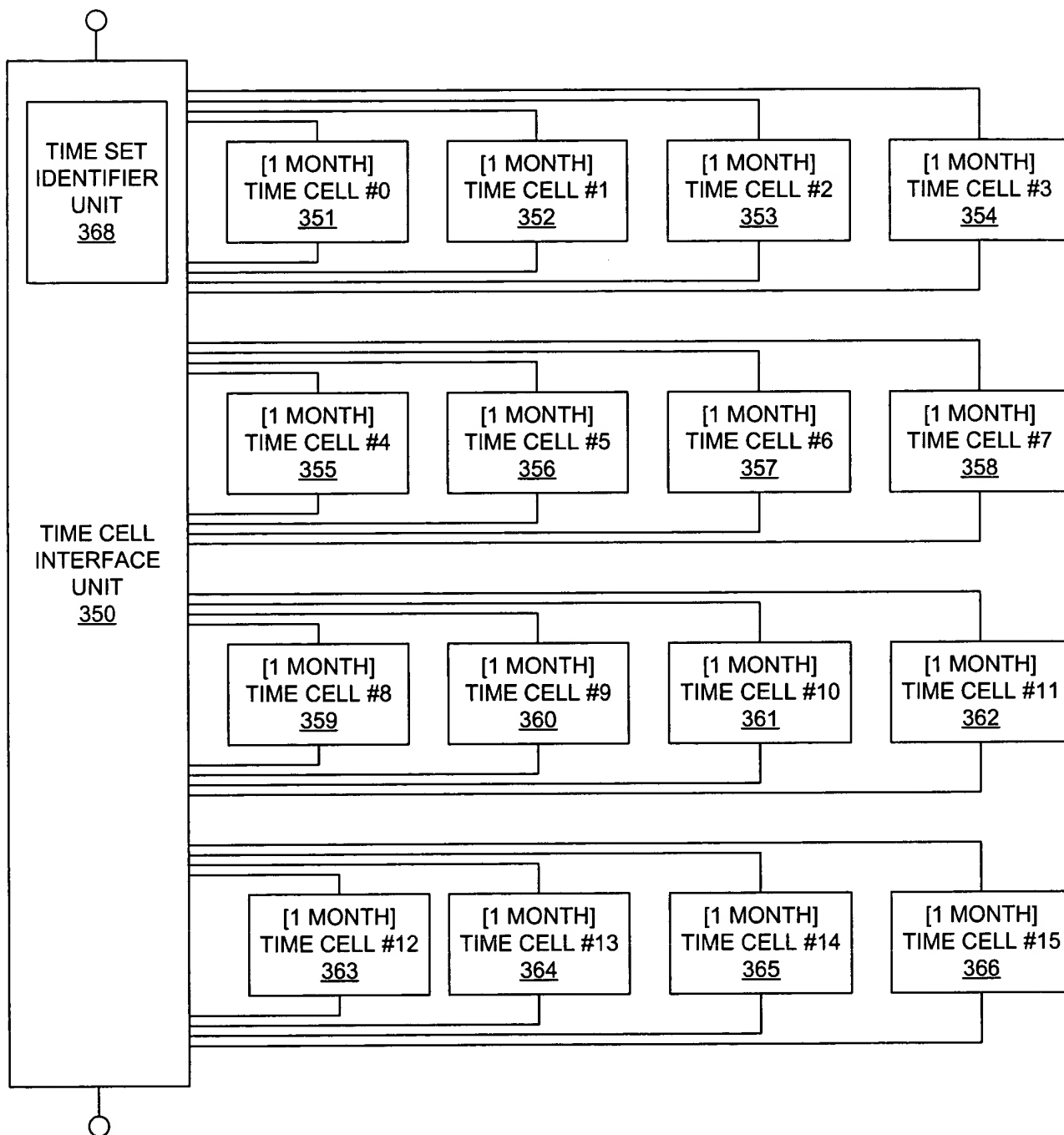


Figure 3C

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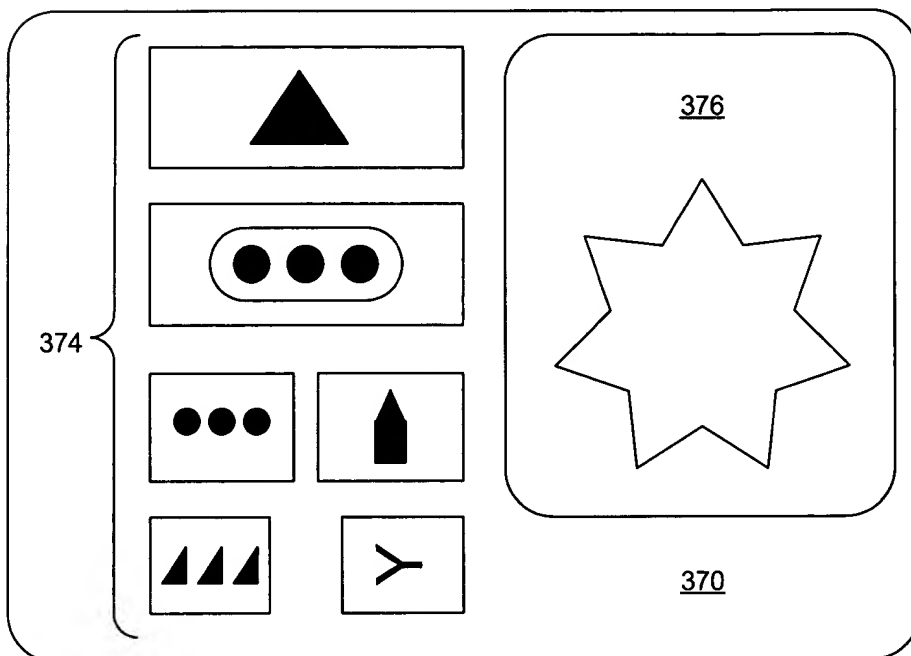


Figure 3D

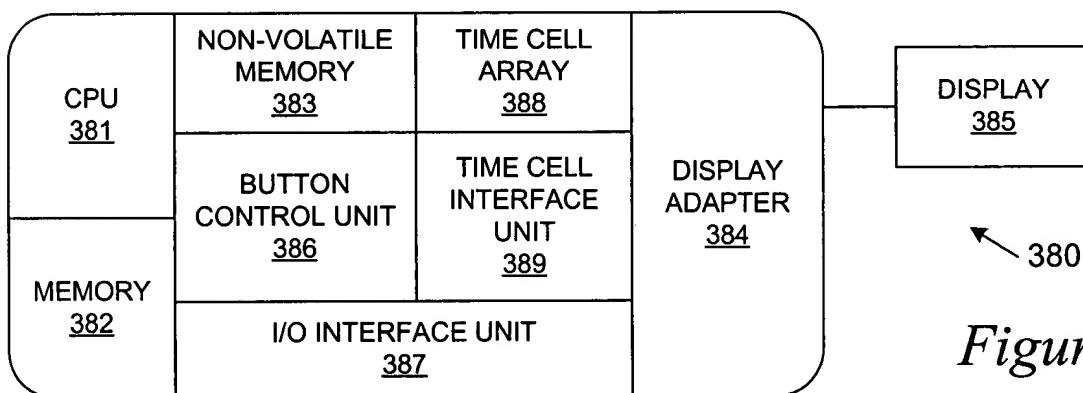


Figure 3E

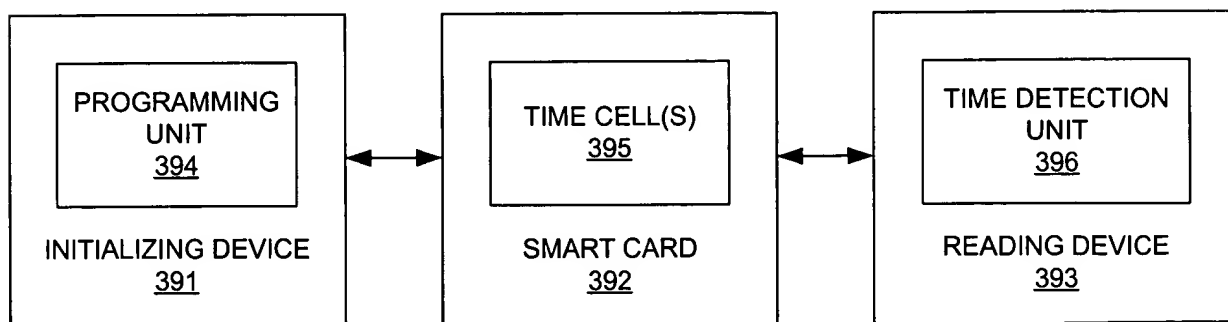


Figure 3F

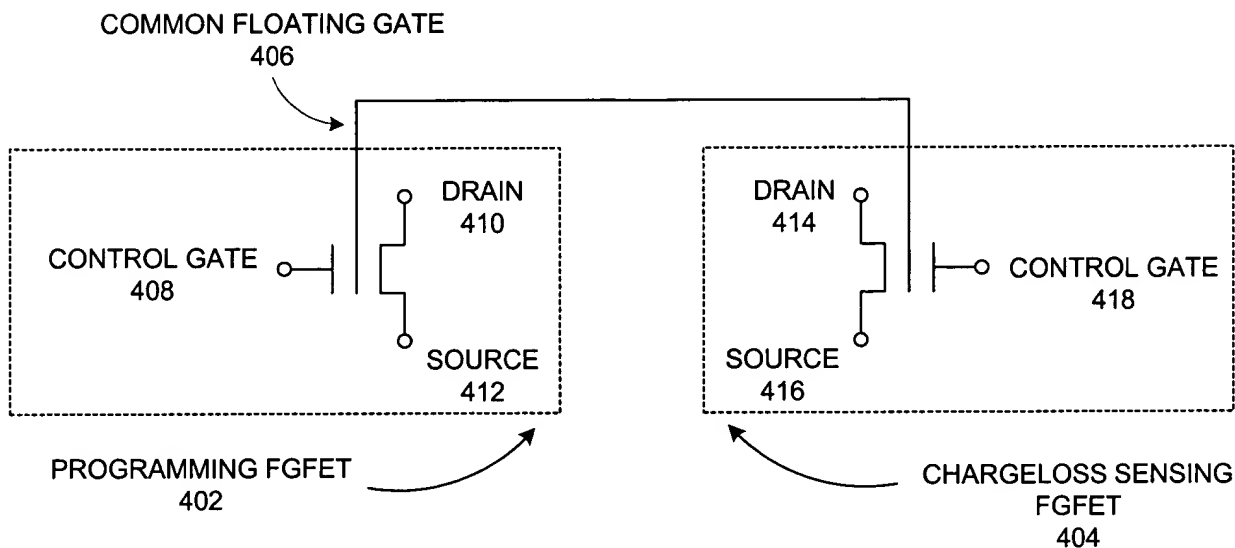


Figure 4A

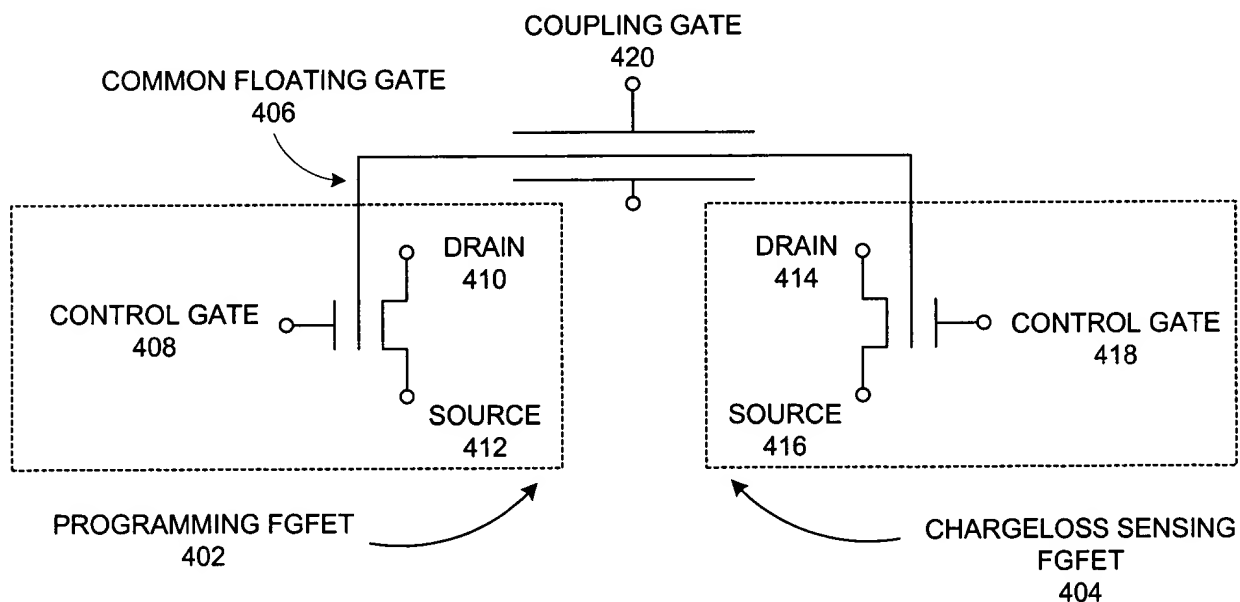


Figure 4B

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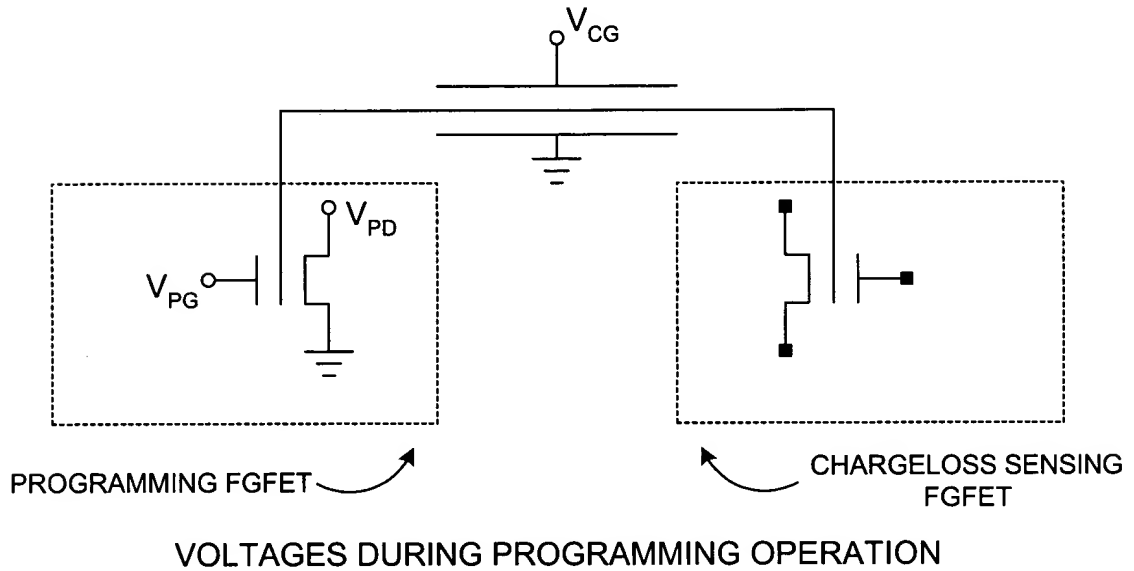


Figure 4C

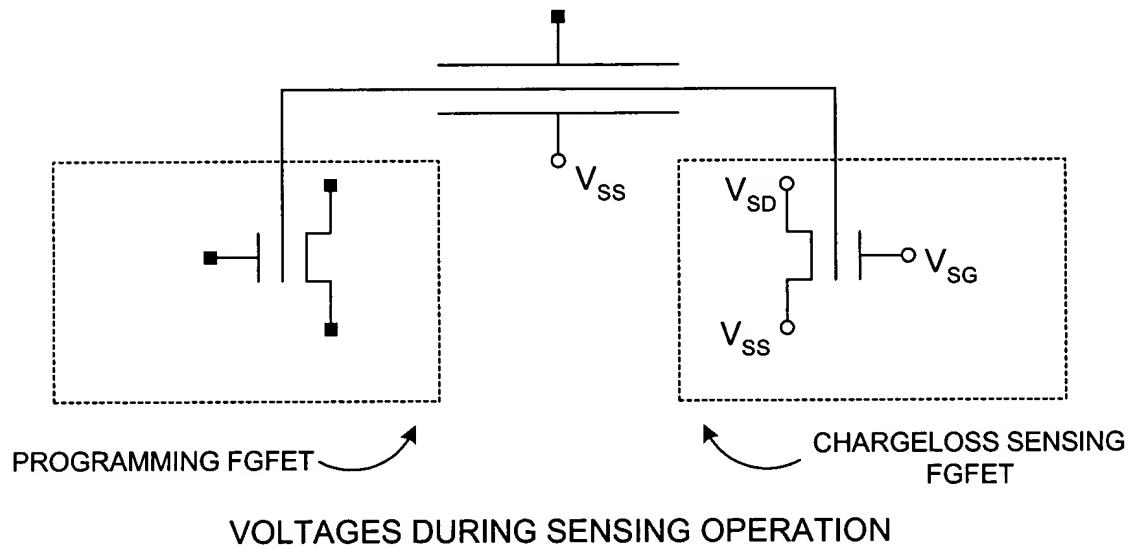


Figure 4D

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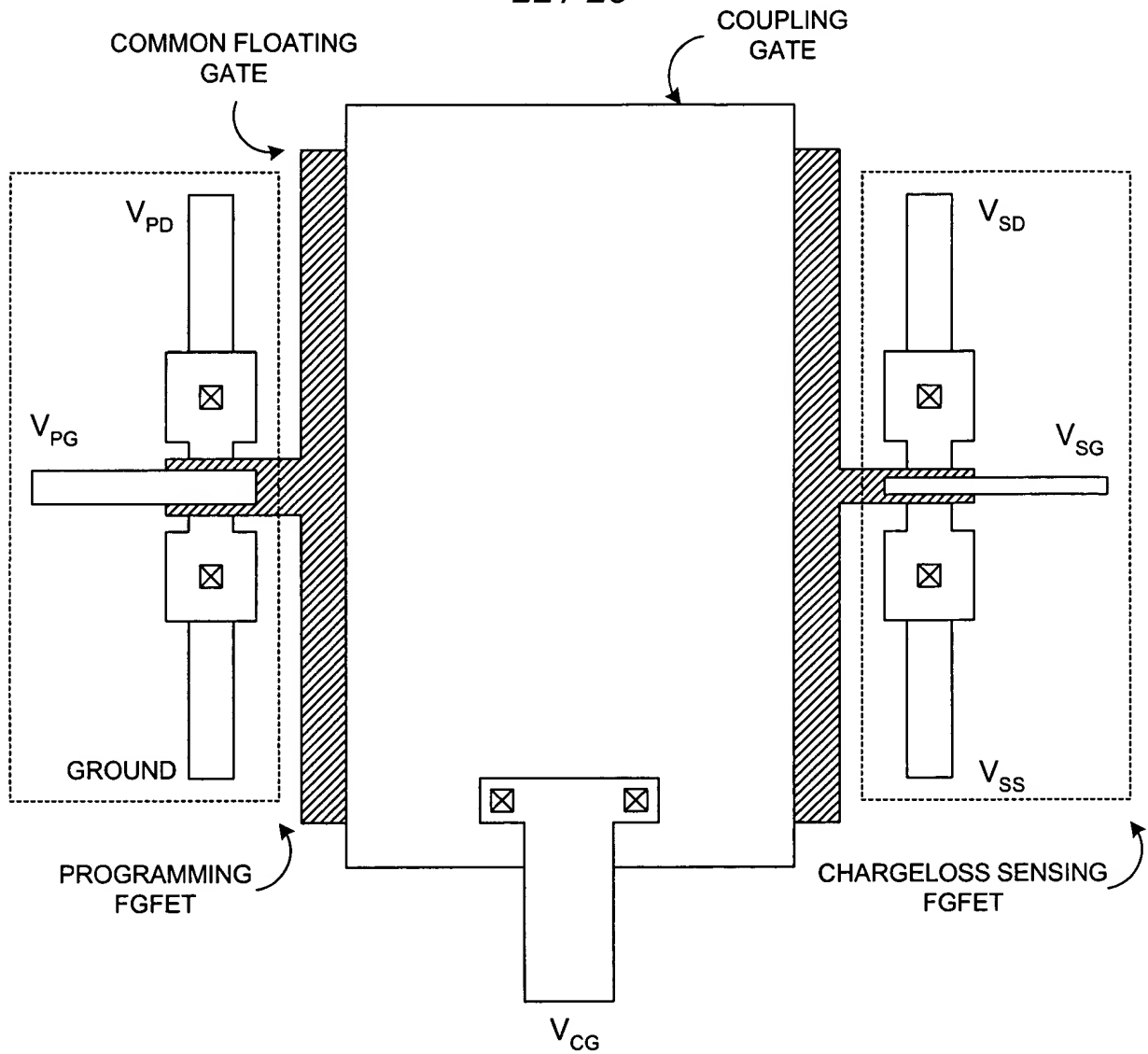


Figure 4E

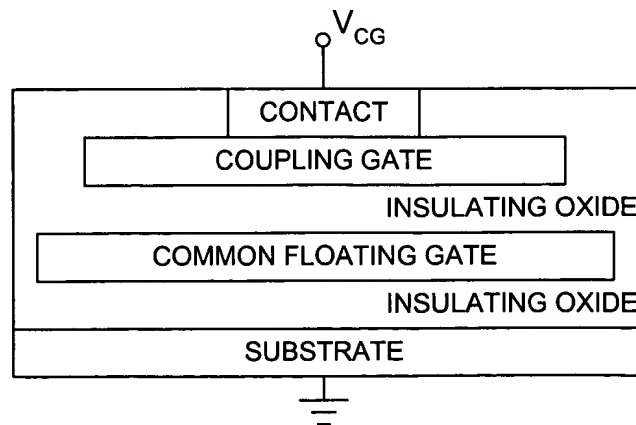
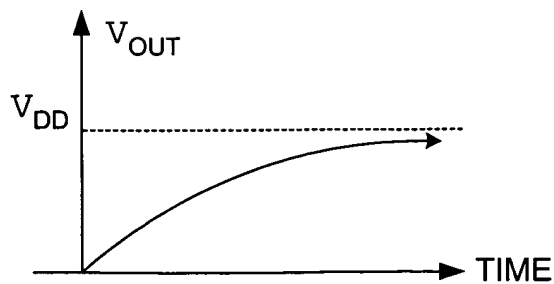
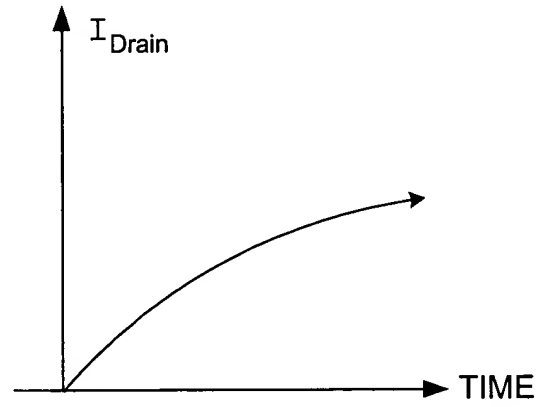
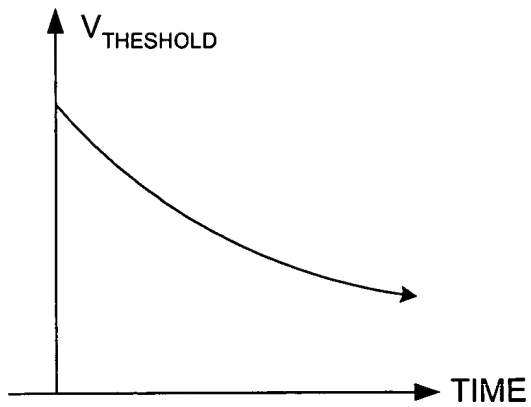
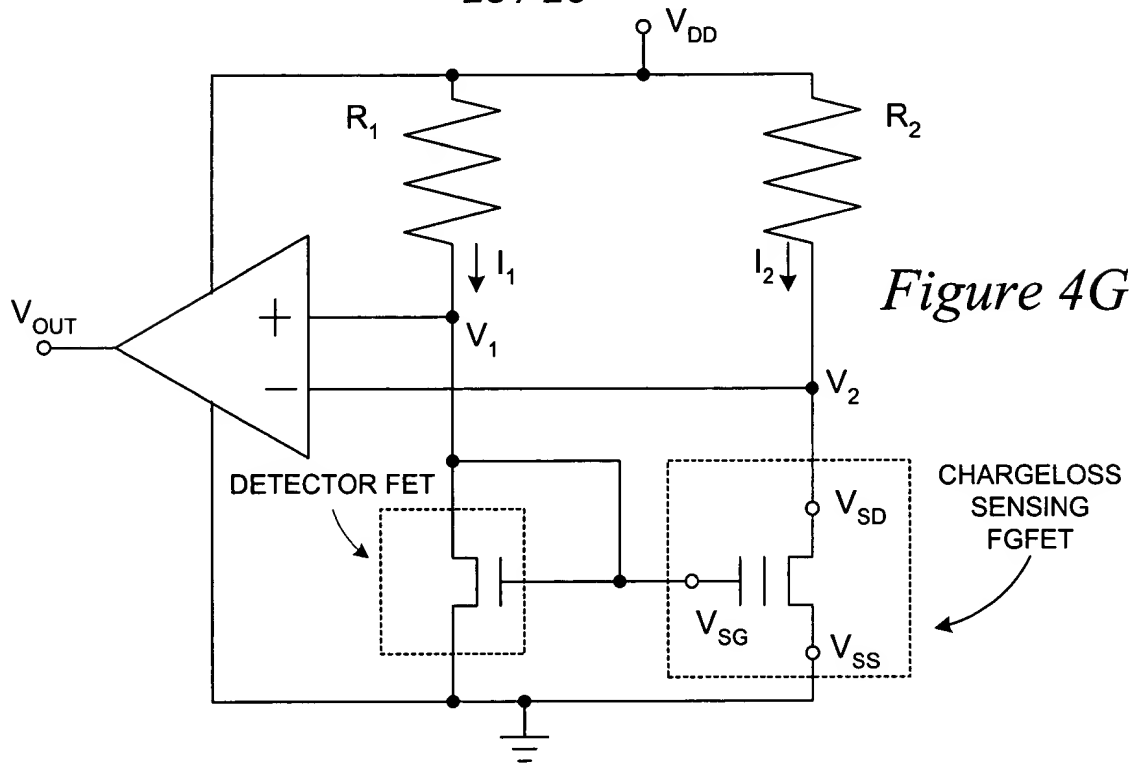


Figure 4F

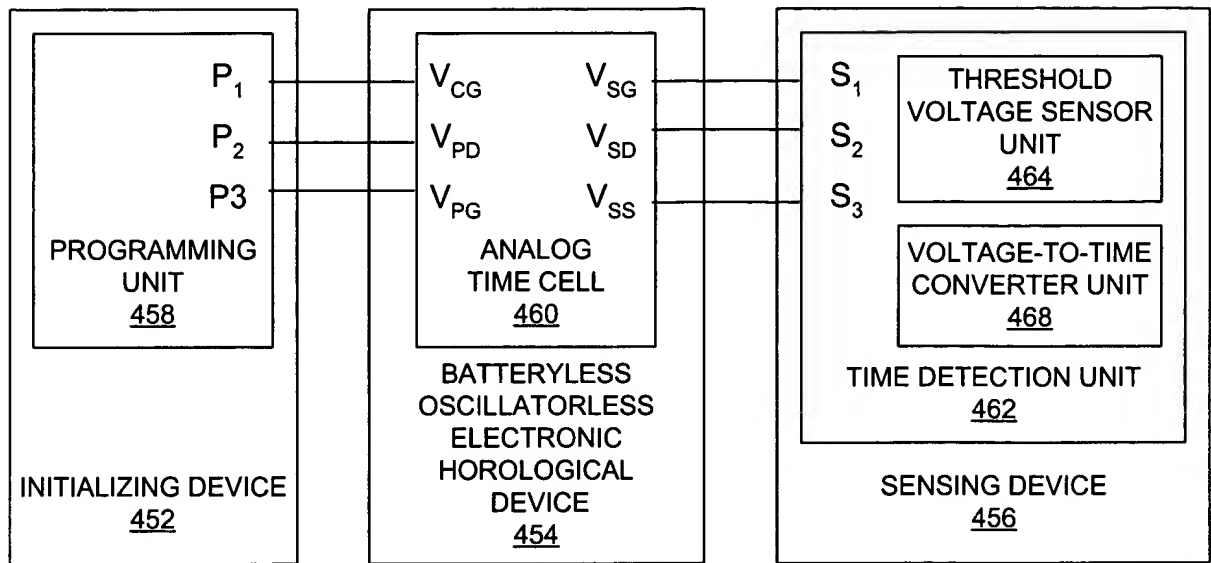
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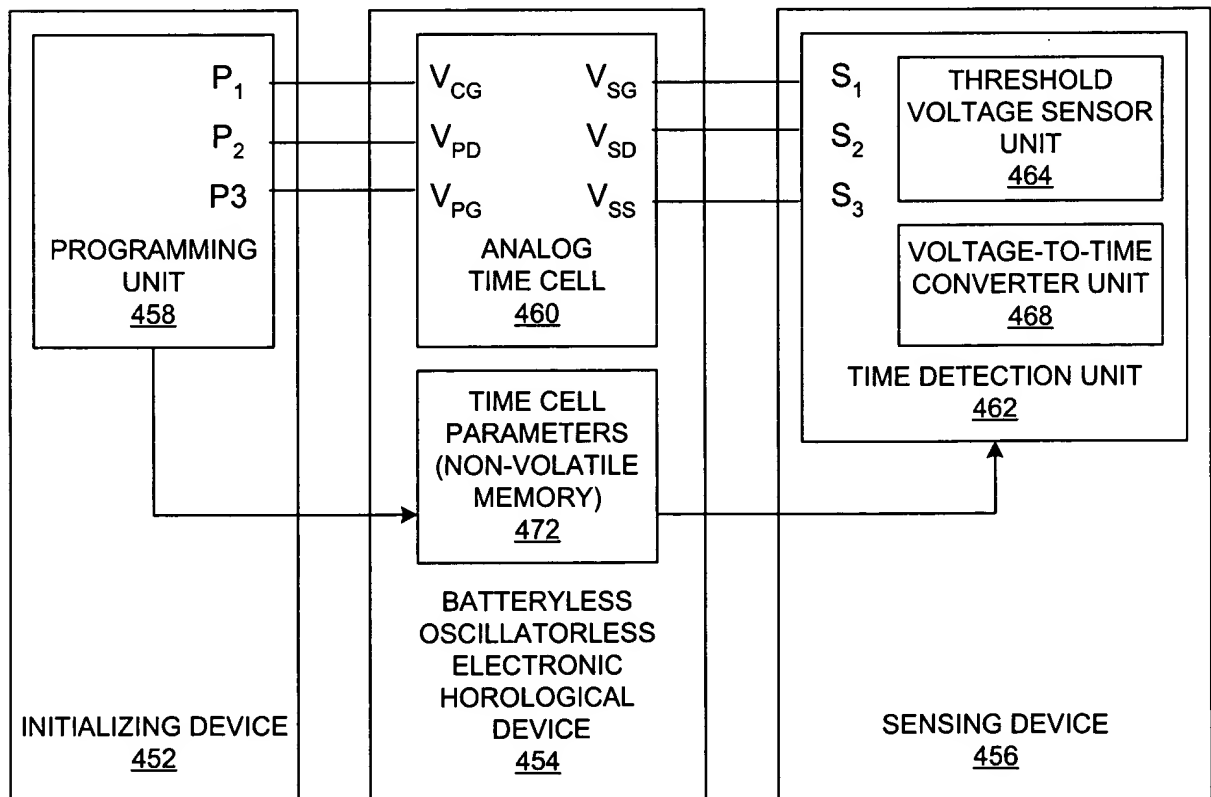
**Batteryless, oscillatorless, binary time cell usable as an horological device
with associated programming methods and devices**

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450 →

*Figure 4K*

470 →

*Figure 4L*

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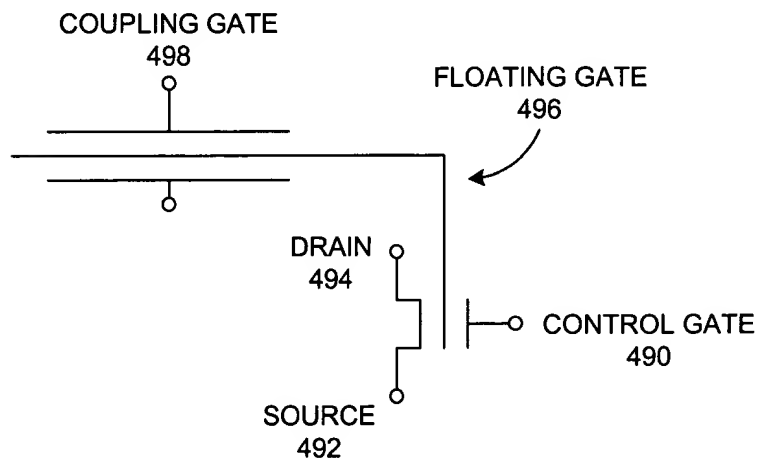


Figure 4M

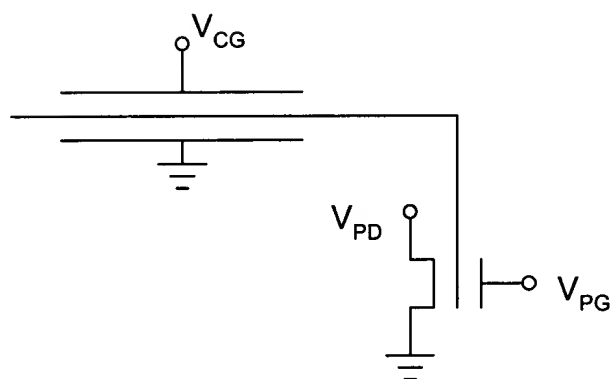


Figure 4N

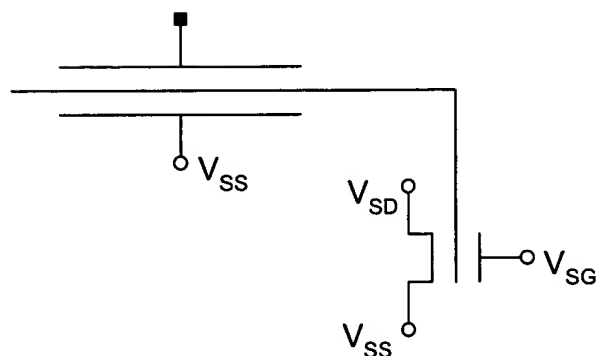


Figure 4O

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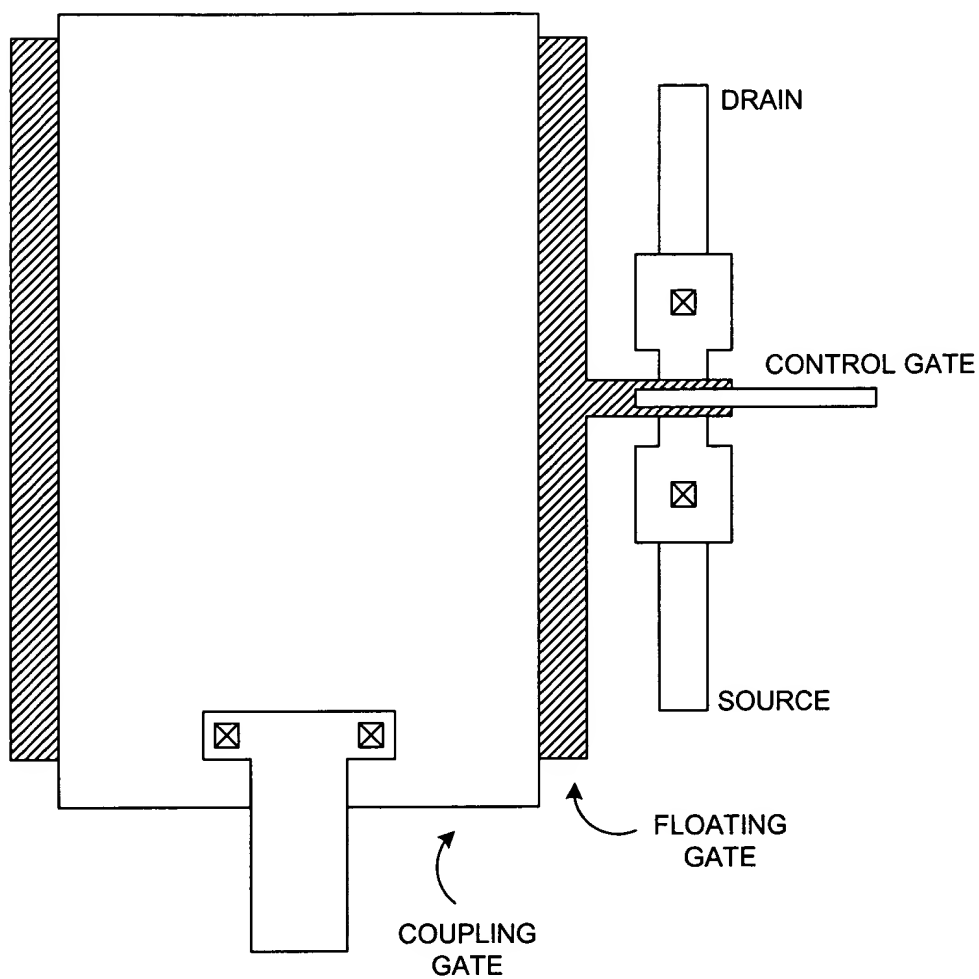


Figure 4P